

IN THE CLAIMS

Claim 1-19 (Canceled).

20 (Previously Presented). An integrated circuit comprising:
a semiconductor structure;
a gate formed on said semiconductor structure; and
a P-type source and a P-type drain region, said source and drain regions including both germanium and a P-type source/drain impurity, said source and drain regions being strained.

21 (Previously Presented). The circuit of claim 20 wherein the ratio of germanium to P-type source/drain impurity is greater than one to one.

22 (Previously Presented). The circuit of claim 20 wherein the ratio of germanium to P-type source/drain impurity is approximately four to one.

23 (Previously Presented). The circuit of claim 20 wherein said source and drain regions are source and drain extensions.

24 (Currently Amended). The circuit of claim 20 wherein said p-type source source/drain region that includes both boron and germanium is a source source/drain extension and wherein said p-type drain region is a drain extension.